

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APM-PWR/08/3674 Notification Date 05/29/2008

SILICON LINE CHANGE FOR BIPOLAR DEVICES - BA21 PRODUCT LINE

PWR - PWR BIP/ IGBT/ RF

Table 1. Change Implementation Schedule

Forecasted implementation date for change	23-Jul-2008
Forecasted availabillity date of samples for customer	22-May-2008
Forecasted date for STMicroelectronics change Qualification Plan results availability	22-May-2008
Estimated date of changed product first shipment	28-Aug-2008

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	See attached list
Type of change	Waferfab process change
Reason for change	Production Optimization
Description of the change	Planar Base Island technology is ready to replace the mature Epibase technology in order to align our products to the actual Market. The line BA21 will replace the old ones B505. Feature: Improved hFE linearity and Higher fT frequency. Benefit: Better performances in switching and linear application.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	See "N" in additional info
Manufacturing Location(s)	

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Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN APM-PWR/08/3674
Please sign and return to STMicroelectronics Sales Office	Notification Date 05/29/2008
□ Qualification Plan Denied	Name:
□ Qualification Plan Approved	Title:
	Company:
□ Change Denied	Date:
□ Change Approved	Signature:
Remark	

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DOCUMENT APPROVAL

Name	Function
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A7/.



Date:	Feb '08
No	07b/08

Reliability evaluation

on

BA21 for silicon line change on TIP35C



Date:	Feb '08
No	07b/08

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Introduction

This report is aimed to qualify the new line BA21 for line change on device TIP35C

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the new line BA21 is qualified.

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Test Vehicles:

Product Line Sales Type Package

BA21 TIP35C TO-247



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Failure Criteria:

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

Parameter Power BIPOLAR Main Parameter

Collector Leakage Current (Icbo or Iceo or Ices, etc...) Emitter Leakage (Iebo) HFE, Vcesat, Vbesat, Vf Breakdown Voltage (BVcbo, BVceo, Vbces, Bvebo)



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Reliability Evaluation Plan and results

D.U.T.: TIP35C LINE: BA21 PACKAGE: TO-247

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 50V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.=150℃ Vdd=80V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot	Parameter deviation within spec. limits at 96 hours.	No parameter deviation out of spec. limits at 96 hours.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot	Parameter deviation within spec. limits at 500 cycles.	No parameter deviation out of spec. limits at 500 cy
THERMAL FATIGUE	ΔTC=70℃ - Pd=24W	77 x 1 Lot	Parameter deviation within spec. limits at 10k cycles.	No parameter deviation out of spec. limits at 10Kcy.

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Technological Characteristics

D.U.T.: TIP35C **PACKAGE: TO-247** LINE: BA21

DIE	Technology: Material: Metallization – Front : - Back :	PLANAR NPN Silicon Al/Si AuAs/Cr/Ni/Au	Passivation : Dimensions :	P-Vapox 4030 x 3680 um ²
DIE ATTACH	Soft Solder	FRAME	Frame and lead material: Frame coating : Lead coating :	Full Ni/NiP except Die Pad Area Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al/Mg Base Al Emitter 7 mils Base 15 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

Ang Mokio (Singapore) AIN SEBAA. (Morocco) **PRODUCTION PLACES**: WAFER PROCESSING:

ASSEMBLY LOCATION: QA LOCATION: AIN SEBAA. (Morocco)

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Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and molding defects.

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatique

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects: improper die-attach, bonding weakness and thermal mismatch among various components of the package.

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